



No.2381

# 2SA1564/2SC4048

PNP/NPN Epitaxial Planar Silicon Transistors

Switching Applications  
(with Bias Resistance)

### Applications

- . Switching circuit, inverter circuit, interface circuit, driver circuit

### Features

- . On-chip bias resistance:  $R_1=10k\Omega, R_2=47k\Omega$
- . Small-sized package: SPA

( ): 2SA1564

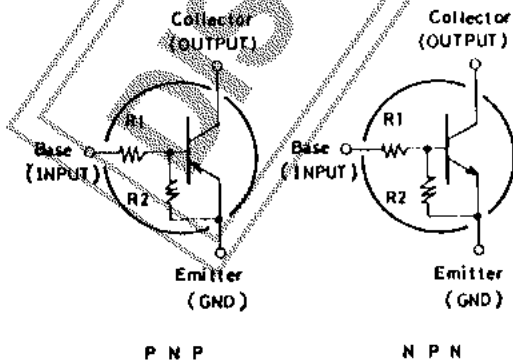
### Absolute Maximum Ratings at $T_a=25^\circ C$

|                              |           |             | unit       |
|------------------------------|-----------|-------------|------------|
| Collector to Base Voltage    | $V_{CB0}$ | (-)50       | V          |
| Collector to Emitter Voltage | $V_{CE0}$ | (-)50       | V          |
| Emitter to Base Voltage      | $V_{EB0}$ | (-)6        | V          |
| Collector Current            | $I_C$     | (-)100      | mA         |
| Collector Current(Pulse)     | $I_{CP}$  | (-)200      | mA         |
| Collector Dissipation        | $P_C$     | 300         | mW         |
| Junction Temperature         | $T_j$     | 150         | $^\circ C$ |
| Storage Temperature          | $T_{stg}$ | -55 to +150 | $^\circ C$ |

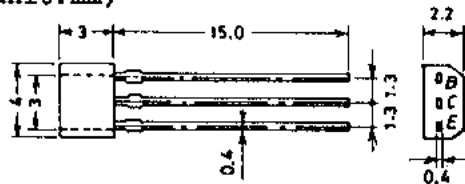
### Electrical Characteristics at $T_a=25^\circ C$

|                          |               |                                  | min    | typ    | max    | unit      |
|--------------------------|---------------|----------------------------------|--------|--------|--------|-----------|
| Collector Cutoff Current | $I_{CB0}$     | $V_{CB}=(-)40V, I_E=0$           |        |        | (-)0.1 | $\mu A$   |
| Collector Cutoff Current | $I_{CE0}$     | $V_{CE}=(-)40V, I_B=0$           |        |        | (-)0.5 | $\mu A$   |
| Emitter Cutoff Current   | $I_{EB0}$     | $V_{EB}=(-)5V, I_C=0$            | (-)67  | (-)88  | (-)125 | $\mu A$   |
| DC Current Gain          | $h_{FE}$      | $V_{CE}=(-)5V, I_C=(-)5mA$       | 70     |        |        |           |
| Gain-Bandwidth Product   | $f_T$         | $V_{CE}=(-)10V, I_C=(-)5mA$      |        | 250    |        | MHz       |
|                          |               |                                  |        | (200)  |        |           |
| Output Capacitance       | $c_{ob}$      | $V_{CB}=(-)10V, f=1MHz$          |        | 3.7    |        | pF        |
|                          |               |                                  |        | (5.5)  |        |           |
| C-E Saturation Voltage   | $V_{CE(sat)}$ | $I_C=(-)10mA, I_B=(-)0.5mA$      | (-)0.1 |        | (-)0.3 | V         |
| C-B Breakdown Voltage    | $V_{(BR)CBO}$ | $I_C=(-)10\mu A, I_E=0$          | (-)50  |        |        | V         |
| C-E Breakdown Voltage    | $V_{(BR)CEO}$ | $I_C=(-)100\mu A, R_{BE}=\infty$ | (-)50  |        |        | V         |
| Input OFF-State Voltage  | $V_{I(off)}$  | $V_{CB}=(-)5V, I_C=(-)100\mu A$  | (-)0.5 | (-)0.7 | (-)0.9 | V         |
| Input ON-State Voltage   | $V_{I(on)}$   | $V_{CE}=(-)0.2V, I_C=(-)5mA$     | (-)0.7 | (-)1.0 | (-)2.0 | V         |
| Input Resistance         | $R_1$         |                                  | 7      | 10     | 13     | $k\Omega$ |
| Resistance Ratio         | $R_1/R_2$     |                                  | 0.193  | 0.213  | 0.234  |           |

### Electrical Connection



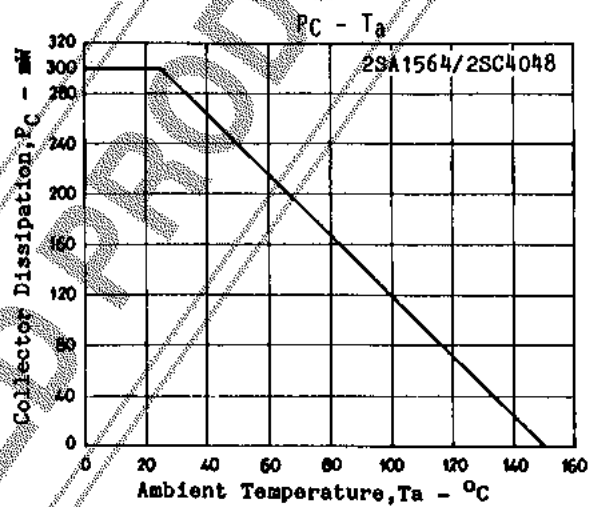
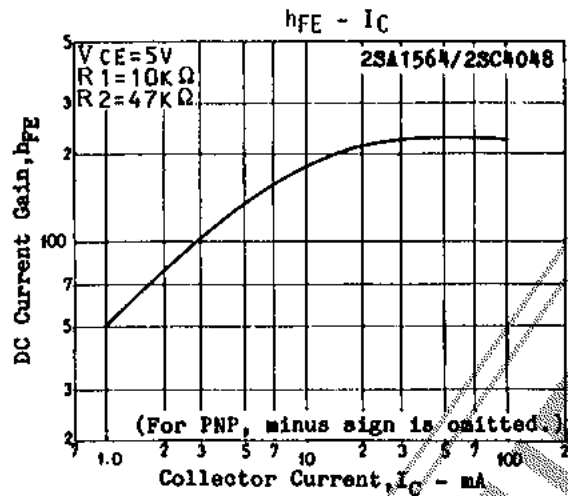
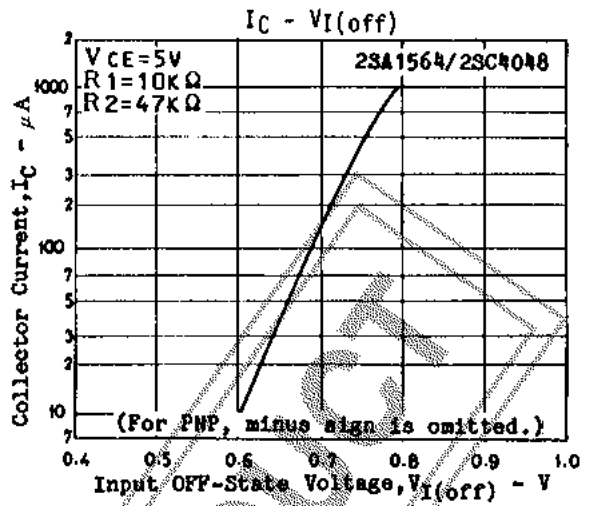
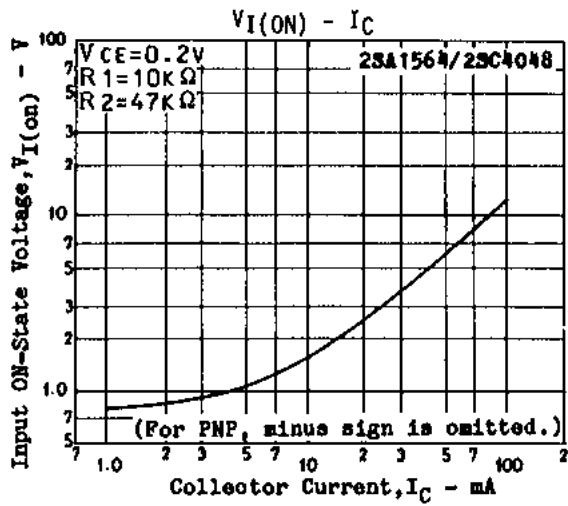
### Case Outline 2033 (unit:mm)



B: Base  
C: Collector  
E: Emitter  
SANYO: SPA

Specifications and information herein are subject to change without notice.

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DISCONTINUED PRODUCT

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